Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT428 (DPAK) surface mountable plastic package intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing with low power drivers and microcontrollers
- · High bidirectional blocking voltage capability
- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate suitable for logic level controls
- Surface mountable package

3. Applications

- General purpose switching and phase control
- Protection circuits
- · Ignition circuits, CDI for 2- and 3-wheelers
- · Motor control e.g. small kitchen appliances

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	800	V
V_{RRM}	repetitive peak reverse voltage			-	-	800	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; $\overline{\text{Fig. 4}}$; $\overline{\text{Fig. 5}}$		-	-	75	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$		-	-	82	Α
Tj	junction temperature		[1]	-	-	125	°C
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 111 °C; <u>Fig. 1</u>		-	-	5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 111 °C; <u>Fig. 2;</u> <u>Fig. 3</u>		-	-	8	Α

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$		-	50	200	μA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 13		50	100	-	V/µs

^[1] Operation above junction temperatures of 110 $^{\circ}$ C may require the use of a gate to cathode resistor of 1 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		A - [
2	Α	anode		Ğ sym037
3	G	gate		symosi
mb	Α	mounting base; connected to anode		
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information

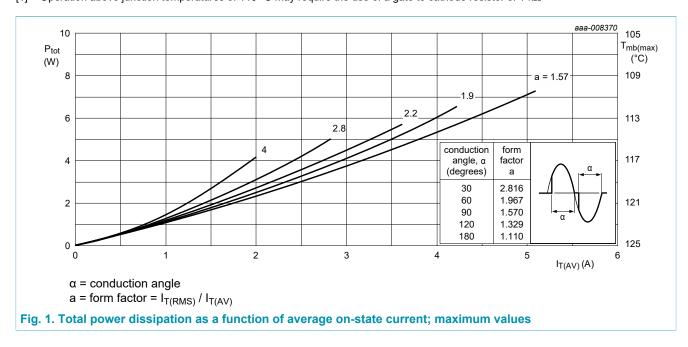
Type number	Package				
	Name	Description	Version		
BT258S-800R	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
V_{RRM}	repetitive peak reverse voltage			-	800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 111 °C; <u>Fig. 1</u>		-	5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	8	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	75	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 ms$		-	82	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse		-	28	A²s
dl _T /dt	rate of rise of on-state current	I _G = 50 mA		-	50	A/µs
I _{GM}	peak gate current			-	2	Α
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature		[1]	-	125	°C

[1] Operation above junction temperatures of 110 $^{\circ}$ C may require the use of a gate to cathode resistor of 1 k Ω



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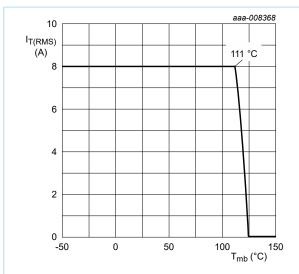


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

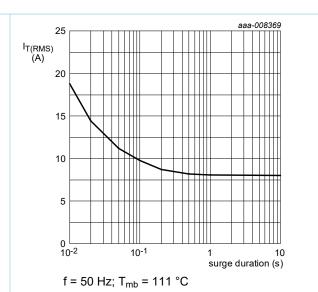


Fig. 3. RMS on-state current as a function of surge duration; maximum values

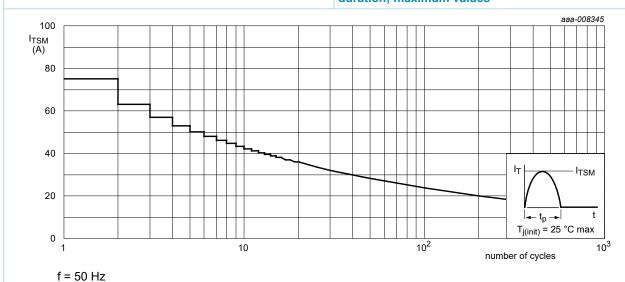
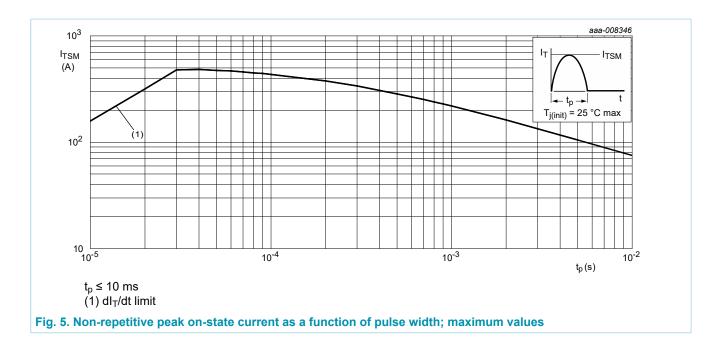


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	Device mounted on an FR4 printed- circuit board, single-sided copper, tin- plated and standard footprint; Fig. 7	-	75	-	K/W

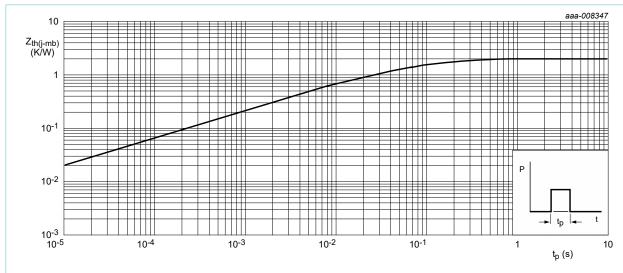
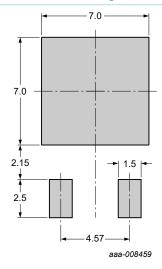


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width



All dimensions are in mm

Plastic meets requirements of UL94 V-O at 3.175 mm

Fig. 7. SOT428: minimum pad sizes for surface-mounting

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			,		
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 8</u>	-	50	200	μΑ
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$	-	0.4	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	0.3	6	mA
V _T	on-state voltage	I _T = 16 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12	-	0.4	1	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 ^{\circ}\text{C};$ Fig. 12	0.1	0.2	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
I _R	reverse current	V _R = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	aracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 13	50	100	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 10 A; V_D = 800 V; I_G = 5 mA; $dI_G/$ dt = 0.2 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 536 V; T_j = 125 °C; I_{TM} = 12 A; V_R = 24 V; $(dI_T/dt)_M$ = 10 A/µs; dV_D/dt = 2 V/µs; $R_{GK(ext)}$ = 1 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

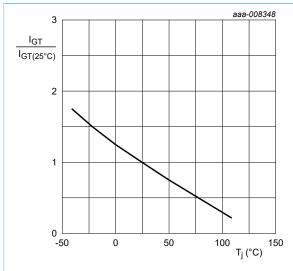


Fig. 8. Normalized gate trigger current as a function of junction temperature

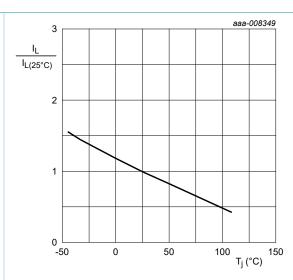


Fig. 9. Normalized latching current as a function of junction temperature

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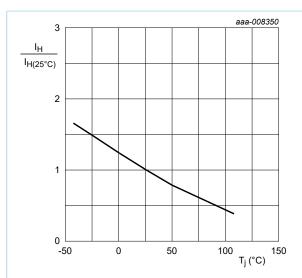
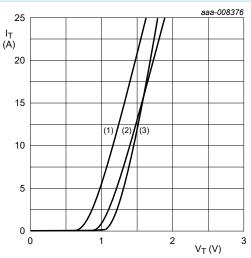


Fig. 10. Normalized holding current as a function of junction temperature



 $V_o = 1.0 \text{ V}; R_s = 0.04 \Omega$

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

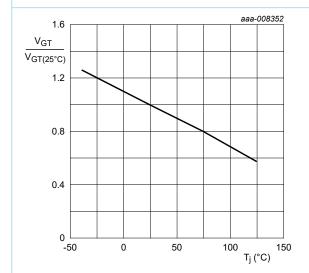


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

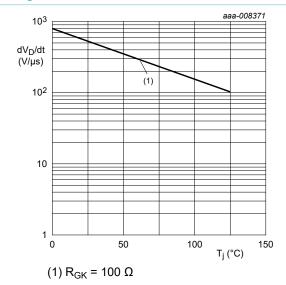
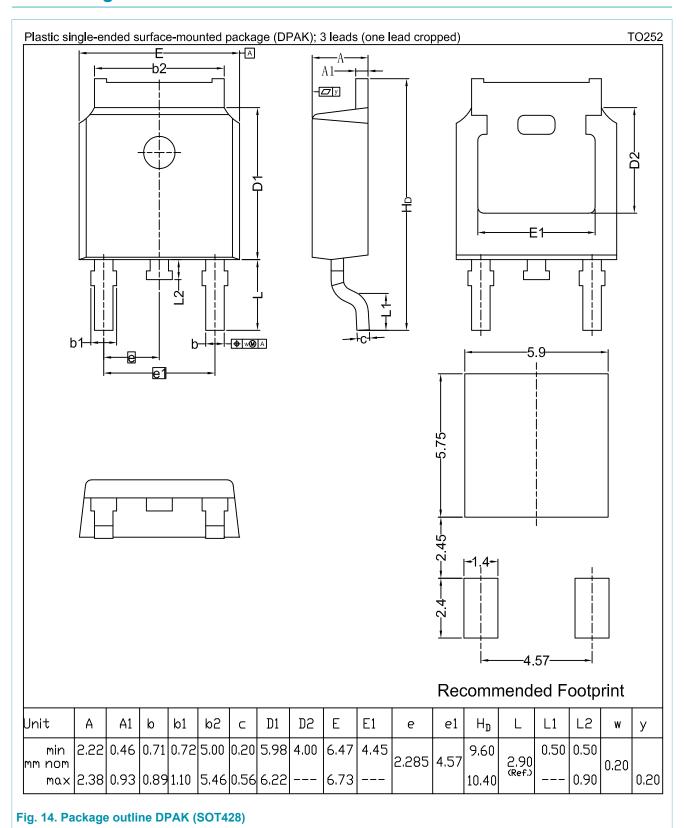


Fig. 13. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline



11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BT258S-800R

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